

N-Channel Enhancement Mode MOSFET

TDM3478

DESCRIPTION

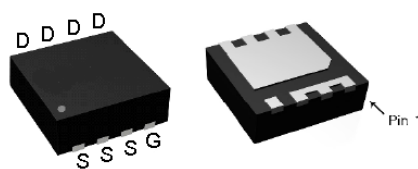
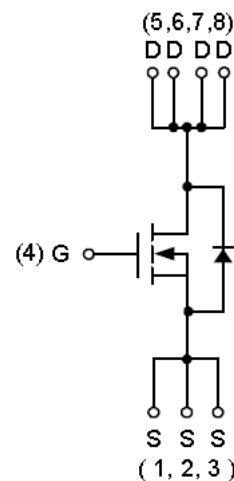
The TDM3478 uses advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

- RDS(ON) < 9.7mΩ @ VGS=4.5V
RDS(ON) < 6mΩ @ VGS=10V
- High Power and current handling capability
- Surface Mount Package
- Lead Free and Green Devices available(RoHS Compliant)

Application

- PWM applications
- Load switch
- Power management
- Powered Systems



DFN3x3-8

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current @ Continuous	I _D (TA=25°C)	15.2	A
	I _D (TA=70°C)	12.1	A
Drain Current @ Current-Pulsed (Note 1)	I _{DM} (Tc=25°C)	100	A
Maximum Power Dissipation (TA=25°C)	P _D	2.08	W
Maximum Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55 To 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance,Junction-to-Ambient (Note 2)	RθJA	60	°C/W
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TDM3478
ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

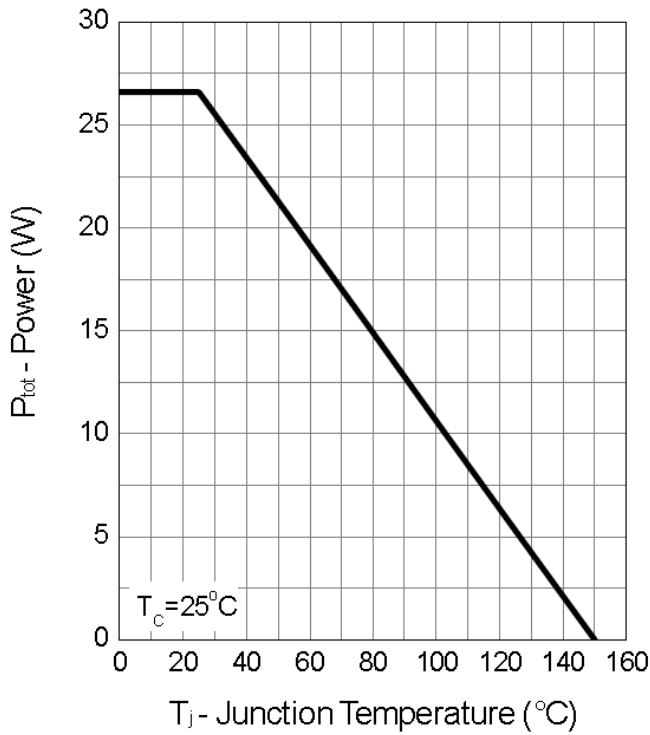
Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 10	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.4	1.7	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=9A$		7.5	9.7	m Ω
		$V_{GS}=10V, I_D=12A$		5	6	m Ω
DYNAMIC CHARACTERISTICS (Note3)						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, F=1.0MHz$		750		PF
Output Capacitance	C_{oss}			530		PF
Reverse Transfer Capacitance	C_{rss}			37		PF
SWITCHING CHARACTERISTICS (Note 3)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=15V, R_L=15\Omega, V_{GEN}=10V, R_G=1\Omega, I_D=1A$		7.8		nS
Turn-on Rise Time	t_r			8.4		nS
Turn-Off Delay Time	$t_{d(off)}$			18		nS
Turn-Off Fall Time	t_f			17		nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=12A, V_{GS}=4.5V$		5.5		nC
Gate-Source Charge	Q_{gs}			1.9		nC
Gate-Drain Charge	Q_{gd}			2.2		nC
Body Diode Reverse Recovery Time	T_{rr}	$I_F=5A, di/dt=100A/\mu s$		11		nS
Body Diode Reverse Recovery Charge	Q_{rr}			13		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 2)	V_{SD}	$V_{GS}=0V, I_S=10A$		0.8	1.1	V

NOTES:

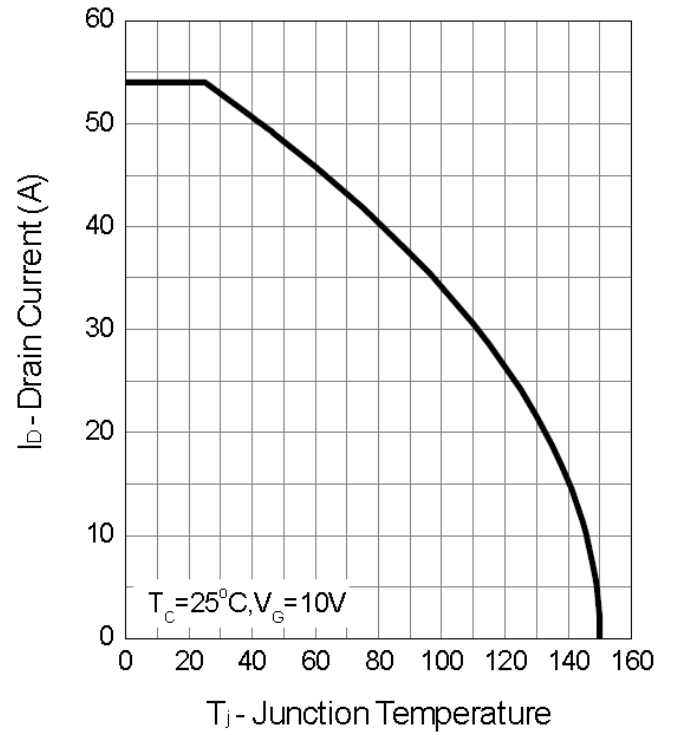
1. Pulse width limited by max. junction temperature.
2. $R_{\theta JA}$ steady state=999s. $R_{\theta JA}$ is measured with the device mounted on 1in2, Fr-4 board with 2oz.Copper
3. Guaranteed by design, not subject to production testing

Typical Operating Characteristics

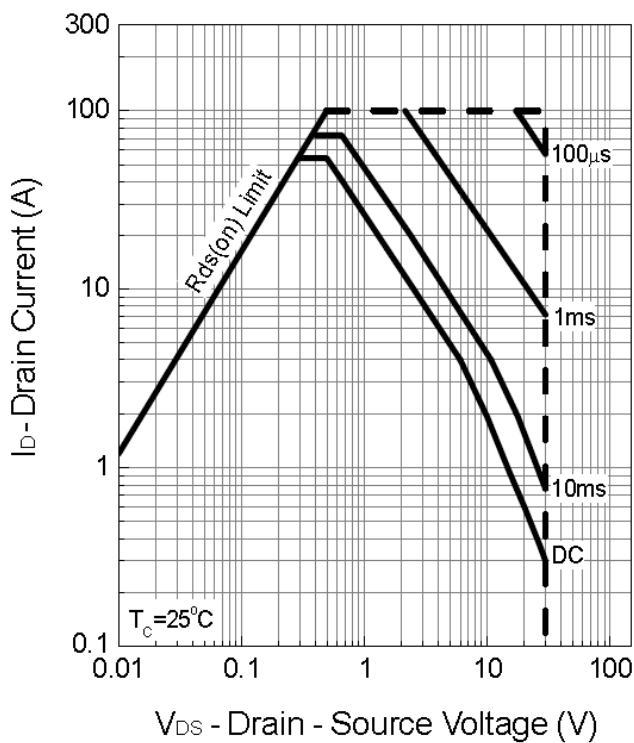
Power Dissipation



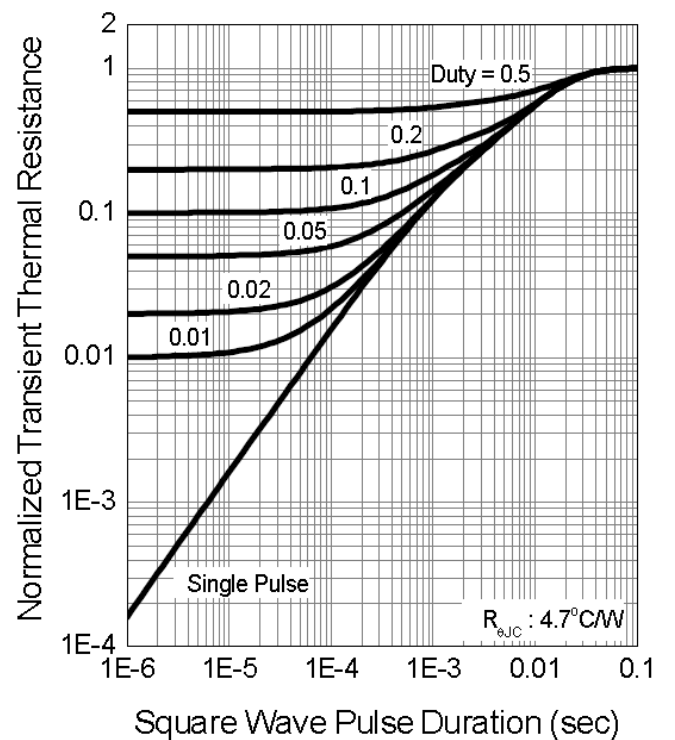
Drain Current



Safe Operation Area

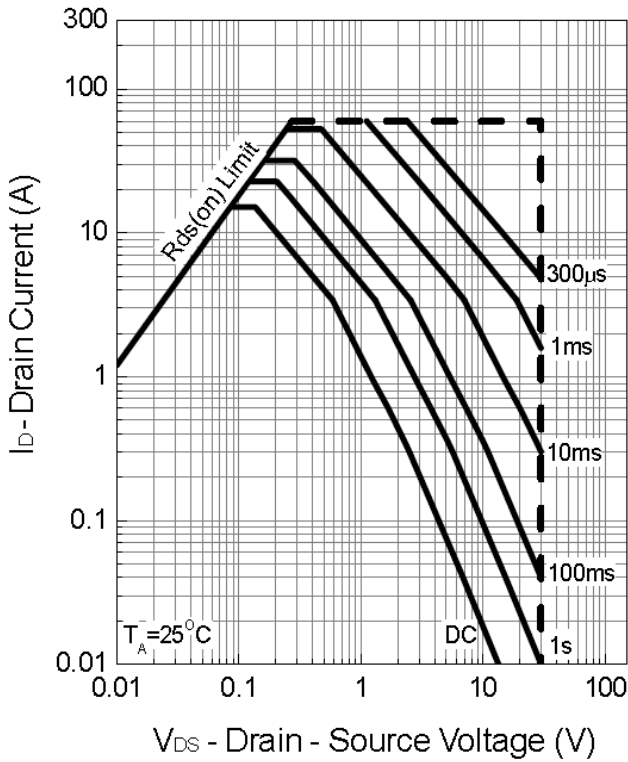


Thermal Transient Impedance

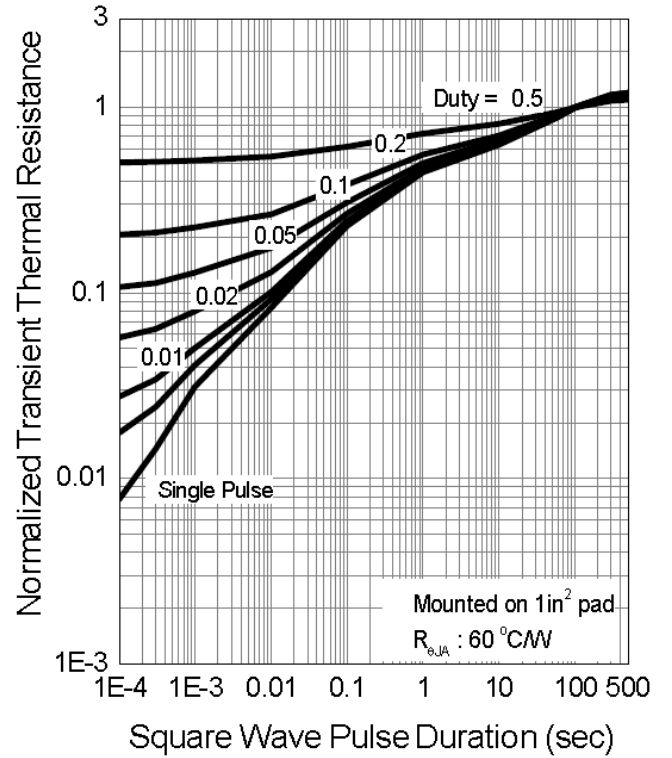


Typical Operating Characteristics(Cont.)

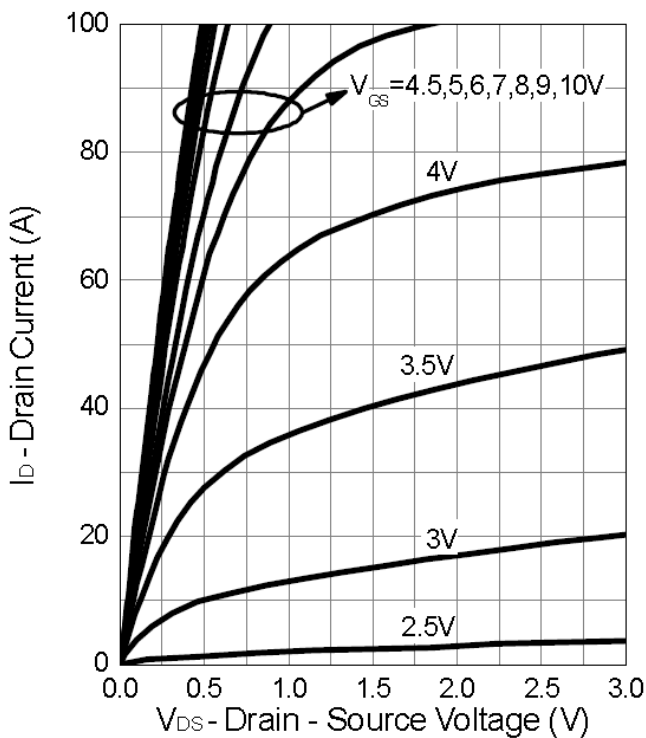
Safe Operation Area



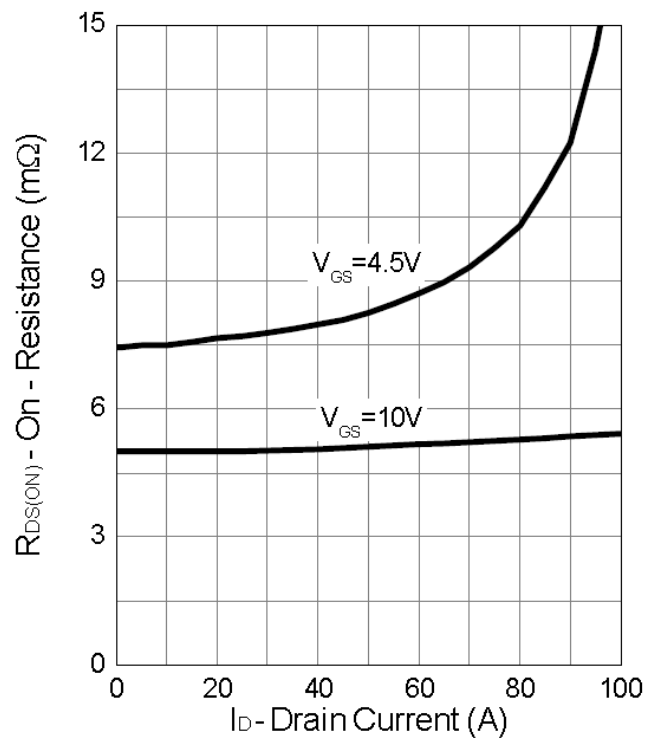
Thermal Transient Impedance



Output Characteristics

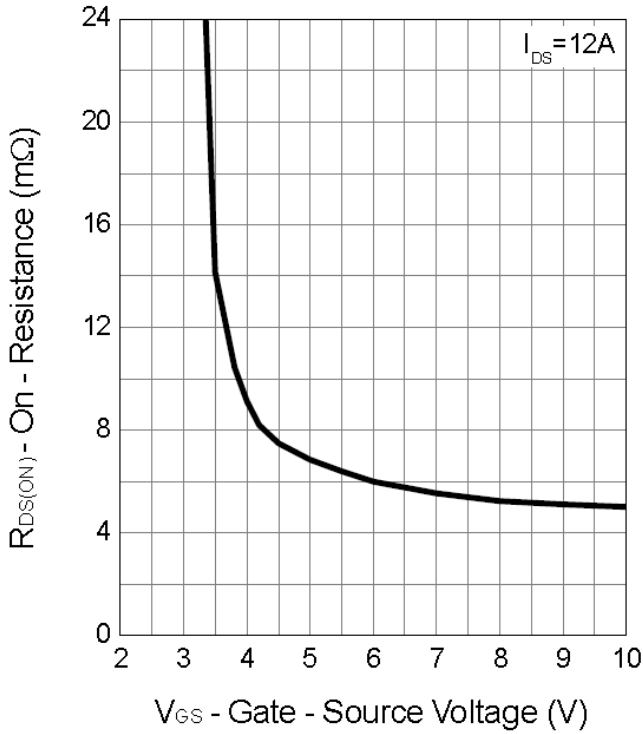


Drain-Source On Resistance

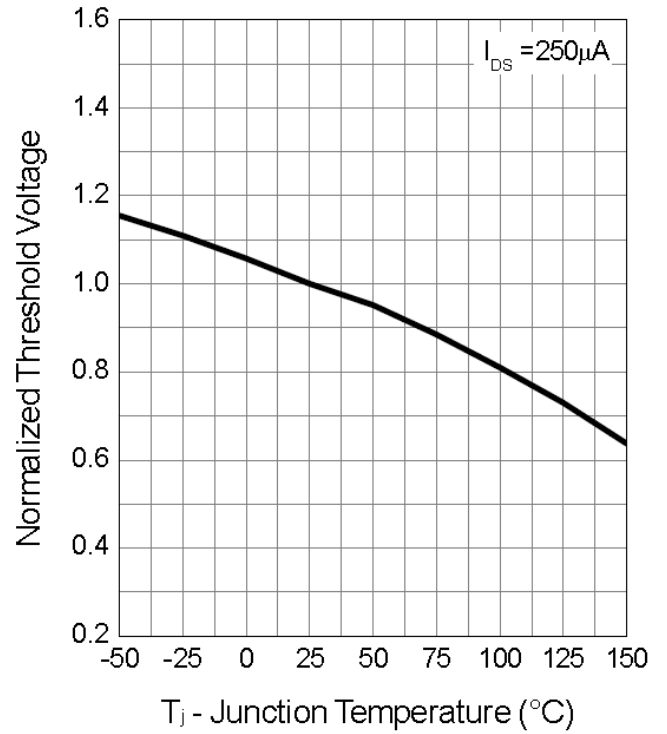


Typical Operating Characteristics (Cont.)

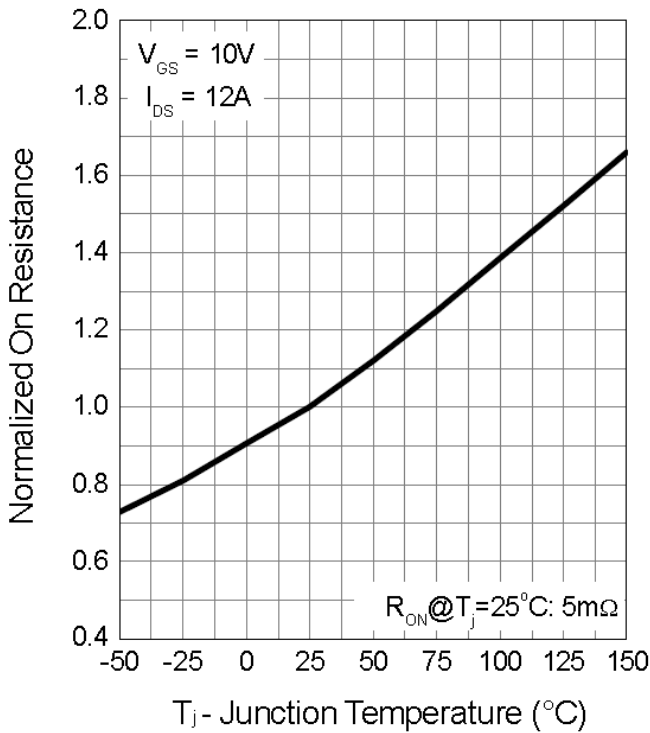
Gate-Source On Resistance



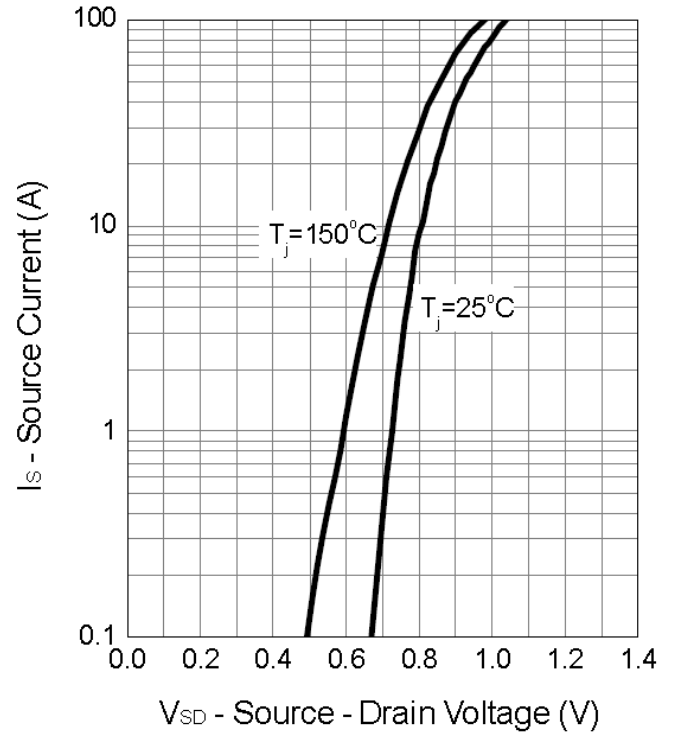
Gate Threshold Voltage



Drain-Source On Resistance

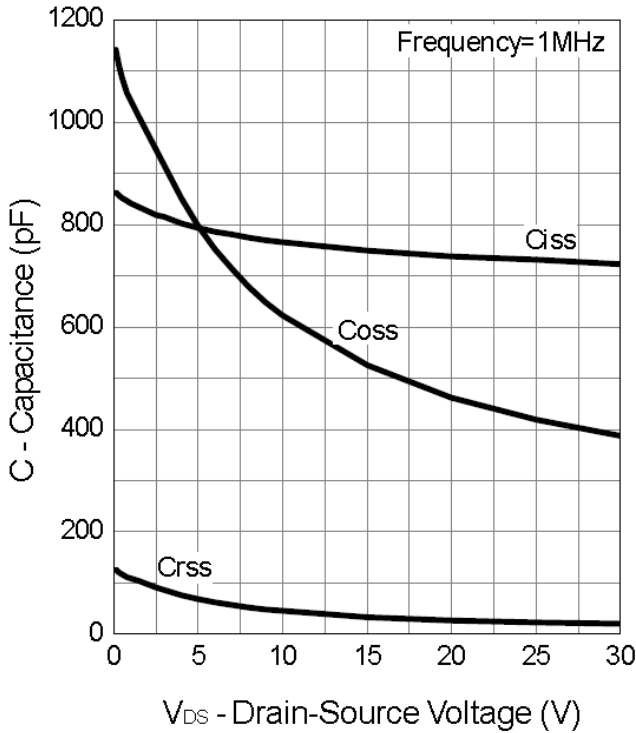


Source-Drain Diode Forward

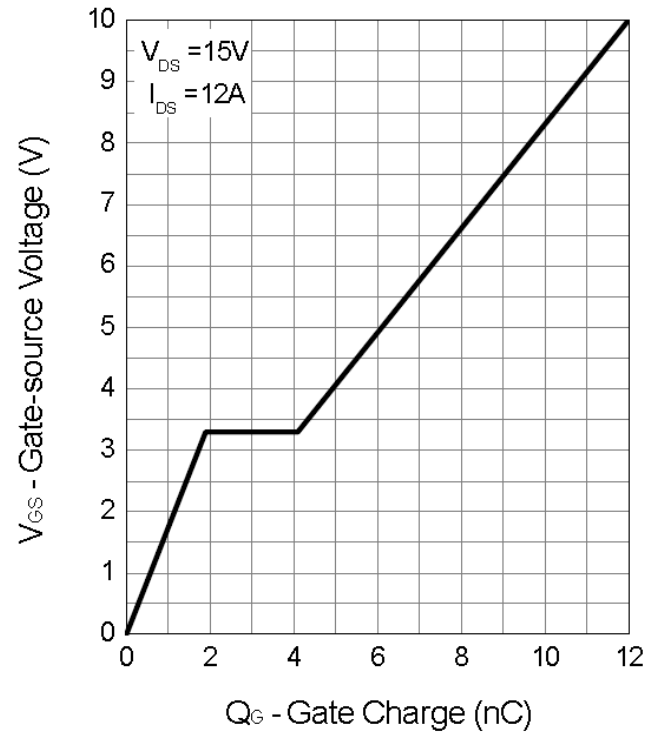


Typical Operating Characteristics (Cont.)

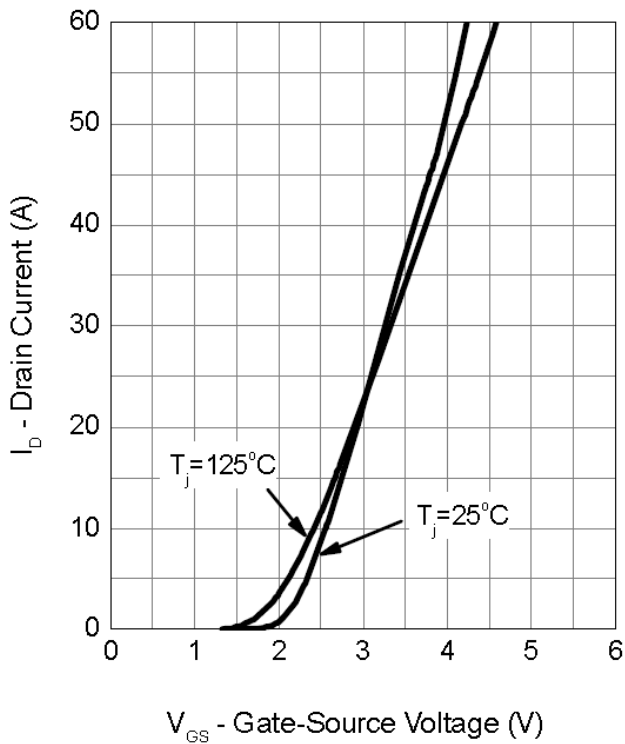
Capacitance



Gate Charge

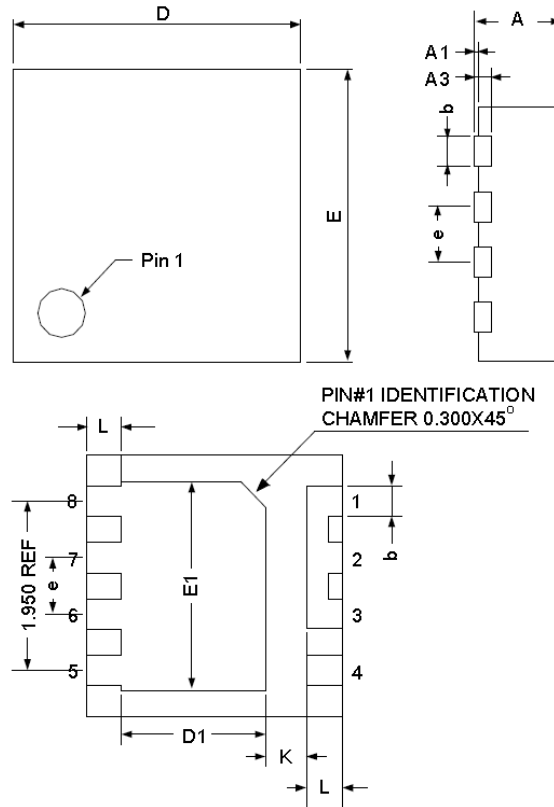


Transfer Characteristics



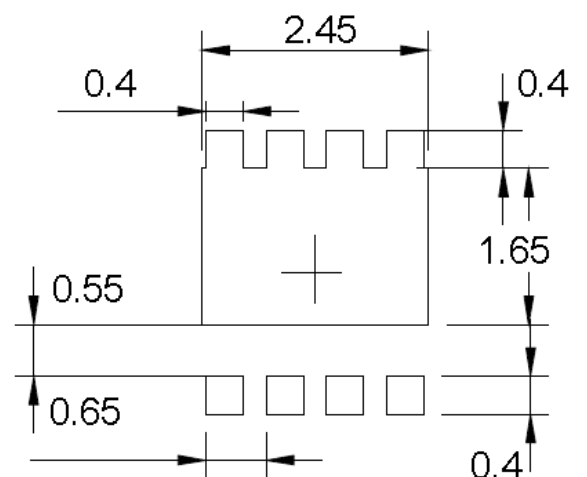
Package Information

DFN3*3-8 Package



SYMBOL	DFN3x3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
A3	0.203 REF		0.008 REF	
b	0.25	0.40	0.010	0.016
D	2.90	3.10	0.114	0.122
E1	2.25	2.55	0.089	0.1
E	2.90	3.10	0.114	0.122
D1	1.65	1.9	0.065	0.075
e	0.65 BSC		0.026 BSC	
L	0.30	0.50	0.012	0.020
K	0.43	-	0.017	-

RECOMMENDED LAND PATTERN



UNIT: mm

Design Notes